

Product Summary

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. Two N Channel MOSFET inside for dual DIE implication.

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A Trench technology

$R_{DS(ON)}$ to minimize conductive loss

G C

Dual DIE in one package

Power Management in Notebook Computer

BLDC Motor driver

Absolute Maximum Ratings $T_C = 25$

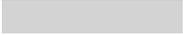
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	45	A
	$I_{D@TC=75}$	34	A
	$I_{D@TC=100}$	28	A
Pulsed Drain Current	I_{DM}	135	A
Total Power Dissipation	$P_D@TC=25$	85	W
Total Power Dissipation	$P_D@TA=25$	3.4	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy	E_{AS}	102	mJ

**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1.5	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	37	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	60			V





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